The RF Line NPN Silicon High-Frequency Transistors

Designed primarily for use in high–gain, low–noise, small–signal UHF and microwave amplifiers constructed with thick and thin–film circuits using surface mount components.

• T1 Suffix Indicates Tape and Reel Packaging of 3,000 Units per Reel.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	12	Vdc
Collector-Base Voltage	VCBO	15	Vdc
Emitter-Base Voltage	V _{EBO}	2.0	Vdc
Collector Current — Continuous	ιc	35	mAdc
Maximum Junction Temperature	T _{Jmax}	150	°C
Power Dissipation, T _{Case} = 75°C (2) Derate linearly above T _{case} = 75°C @	PD(max)	0.306 4.08	W mW/°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Storage Temperature	T _{stg}	-55 to +150	°C
Thermal Resistance Junction to Case	R _θ JC	245	°C/W

DEVICE MARKING

BFR93ALT1 = R2

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

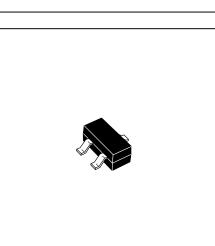
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (1) $(I_C = 10 \text{ mA})$	V(BR)CEO	12	_	Vdc
Collector–Base Breakdown Voltage $(I_C = 10 \ \mu A)$	V(BR)CBO	15	_	Vdc
Emitter–Base Breakdown Voltage ($I_C = 100 \ \mu A$)	V(BR)EBO	2.0	_	Vdc
Collector Cutoff Current ($V_{CE} = 10 V$)	ICEO	_	50	nA
Collector Cutoff Current ($V_{CB} = 10 V$)	ІСВО	_	50	nA
ON CHARACTERISTICS			- -	

DC Current Gain (1) (I _C = 30 mA, V _{CE} = 5.0 V)	hFE	40	_	—
Collector–Emitter Saturation Voltage (1) (I _C = 35 mA, I _B = 7.0 mA)	VCE(sat)	_	0.5	Vdc
Base–Emitter Saturation Voltage (1) ($I_C = 35 \text{ mA}, I_B = 7.0 \text{ mA}$)	VBE(sat)	—	1.2	Vdc

NOTES:

1. Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.

2. Case temperature measured on collector lead immediately adjacent to body of package.



BFR93ALT1

RF TRANSISTORS NPN SILICON

CASE 318–08, STYLE 6 SOT–23

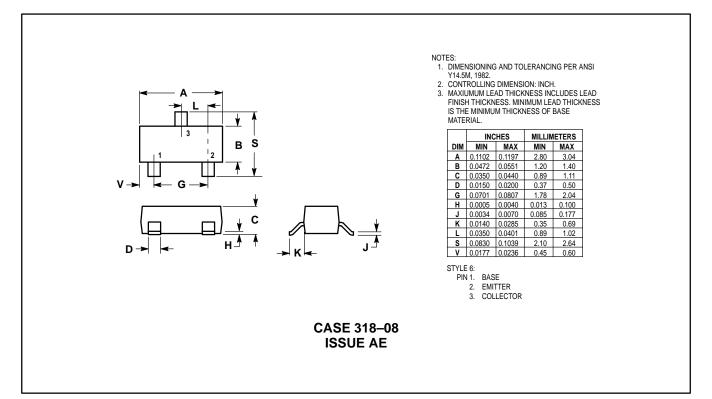
LOW PROFILE



ELECTRICAL CHARACTERISTICS — continued (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ($I_C = 30 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 500 \text{ MHz}$)	fΤ	3.0	—	GHz
Noise Figure (V _{CE} = 5.0 V, I _C = 2.0 mA, R _S = 50 Ω , f = 30 MHz)	NF		3.0	dB

PACKAGE DIMENSIONS



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